

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| 1 | 95 | ((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:05 |
| 2 | 13 | ((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicon or si) with substrate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:01 |
| 3 | 72 | ((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicon or si) with substrate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:09 |
| 4 | 54 | ((substrate near (trench or via)) and ((trench or via) near (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum))) and ((silicon or si) with substrate)) and (@ad<20010501) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:39 |
| 5 | 0 | (substrate near (trench or via)) and ((trench or via) near (trench or via or groove) near (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:40 |
| 6 | 10 | (substrate near (trench or via)) and ((trench or via) near (trench or via or groove) with (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:37 |
| 7 | 576 | 257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 16:39 |
| 8 | 459 | (257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:06 |
| 9 | 350 | ((257/758.ccls. and (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)) and (trench or via or groove) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:03 |
| 10 | 1342 | trench adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:04 |
| 11 | 629 | (trench adj gate) and (gate near oxide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:04 |
| 12 | 725 | (trench adj gate) and (gate near (oxide or sio or dielectric)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:05 |
| 13 | 260 | ((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:06 |
| 14 | 206 | ((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:06 |

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| 15 | 117 | (((((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)) and ((gate or trench) with (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:12 |
| 16 | 50 | (((((trench adj gate) and (gate near (oxide or sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)) and ((gate or trench) with (SiN or (etch adj stop) or Ta or TaN or Wn or WN or tantalum)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/02 17:12 |
| - | 2 | ((("5268326") or ("5091330")).PN. | USPAT; US-PGPUB | 2003/01/02 15:55 |